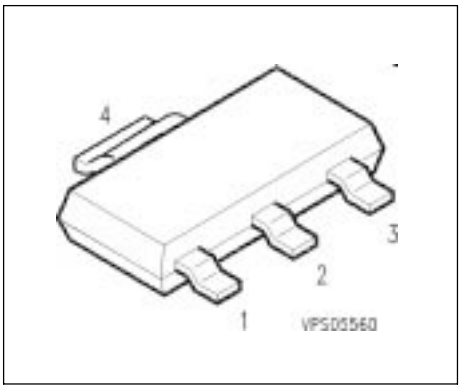
SIPMOS ® Small-Signal Transistor

- P channel
- Enhancement mode
- Logic Level
- Avalanche rated
- $V_{GS(th)}$ = -0.8...-2.0 V



Pin 1	Pin 2	Pin 3	Pin 4
G	D	S	D

Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Marking
BSP 171	-60 V	-1.7 A	0.35 Ω	SOT-223	BSP 171

Type	Ordering Code	Tape and Reel Information
BSP 171	Q67000-S224	E6327

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current T_A = 24 °C	I_D	-1.7	A
DC drain current, pulsed T_A = 25 °C	I_{Dpuls}	-6.8	
Avalanche energy, single pulse I_D = -1.7 A, V_{DD} = -25 V, R_{GS} = 25 Ω L = 3.23 mH, T_j = 25 °C	E_{AS}	8	mJ
Gate source voltage	V_{GS}	± 20	V
Power dissipation T_A = 25 °C	P_{tot}	1.8	W

Maximum Ratings

Parameter	Symbol	Values	Unit
Chip or operating temperature	T_j	-55 ... + 150	°C
Storage temperature	T_{stg}	-55 ... + 150	
Thermal resistance, chip to ambient air 1)	R_{thJA}	≤ 70	K/W
Thermal resistance, junction-soldering point 1)	R_{thJS}	≤ 10	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

1) Transistor on epoxy pcb 40 mm x 40 mm x 1,5 mm with 6 cm^2 copper area for drain connection

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage V_{GS} = 0 V, I_D = -0.25 mA, T_j = 25 °C	$V_{(BR)DSS}$	-60	-	-	V
Gate threshold voltage V_{GS}=V_{DS}, I_D = -1 mA	$V_{GS(th)}$	-0.8	-1.4	-2	
Zero gate voltage drain current V_{DS} = -60 V, V_{GS} = 0 V, T_j = 25 °C V_{DS} = -60 V, V_{GS} = 0 V, T_j = 125 °C	I_{DSS}	- -	-0.1 -10	-1 -100	µA
Gate-source leakage current V_{GS} = -20 V, V_{DS} = 0 V	I_{GSS}	-	-10	-100	nA
Drain-Source on-state resistance V_{GS} = -10 V, I_D = -1.7 A	$R_{DS(on)}$	-	0.22	0.35	Ω

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

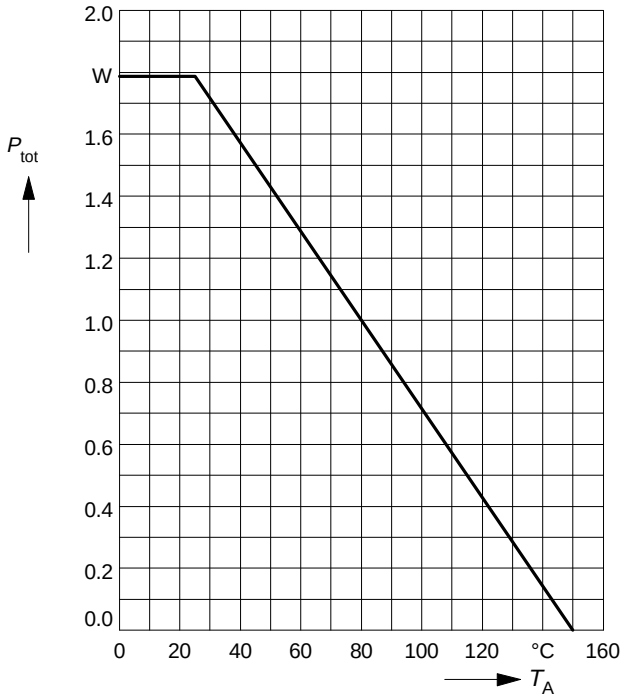
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, I_D = -1.7 A	g_{fs}	1	1.55	-	S
Input capacitance V_{GS} = 0 V, V_{DS} = -25 V, f = 1 MHz	C_{iss}	-	720	960	pF
Output capacitance V_{GS} = 0 V, V_{DS} = -25 V, f = 1 MHz	C_{oss}	-	290	435	
Reverse transfer capacitance V_{GS} = 0 V, V_{DS} = -25 V, f = 1 MHz	C_{rss}	-	120	180	
Turn-on delay time V_{DD} = -30 V, V_{GS} = -10 V, I_D = -0.3 A R_{GS} = 50 Ω	$t_{d(on)}$	-	16	25	ns
Rise time V_{DD} = -30 V, V_{GS} = -10 V, I_D = -0.3 A R_{GS} = 50 Ω	t_r	-	70	105	
Turn-off delay time V_{DD} = -30 V, V_{GS} = -10 V, I_D = 0.3 A R_{GS} = 50 Ω	$t_{d(off)}$	-	230	310	
Fall time V_{DD} = -30 V, V_{GS} = -10 V, I_D = -0.3 A R_{GS} = 50 Ω	t_f	-	280	375	

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current T_A = 25 °C	I_S	-	-	-1.7	A
Inverse diode direct current,pulsed T_A = 25 °C	I_{SM}	-	-	-6.8	
Inverse diode forward voltage V_{GS} = 0 V, I_F = -3.4 A, T_j = 25 °C	V_{SD}	-	-0.9	-1.2	V
Reverse recovery time V_R = 30 V, I_F=I_S = 0 , di_F/dt = 100 A/µs	t_{rr}	-	300	-	ns
Reverse recovery charge V_R = 30 V, I_F=I_S = 0 , di_F/dt = 100 A/µs	Q_{rr}	-	0.82	-	µC

Power dissipation

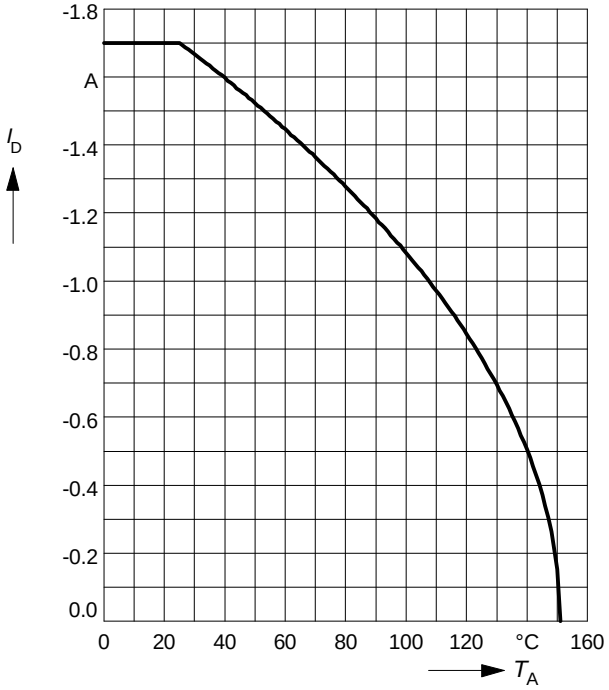
$P_{tot} = f(T_A)$



Drain current

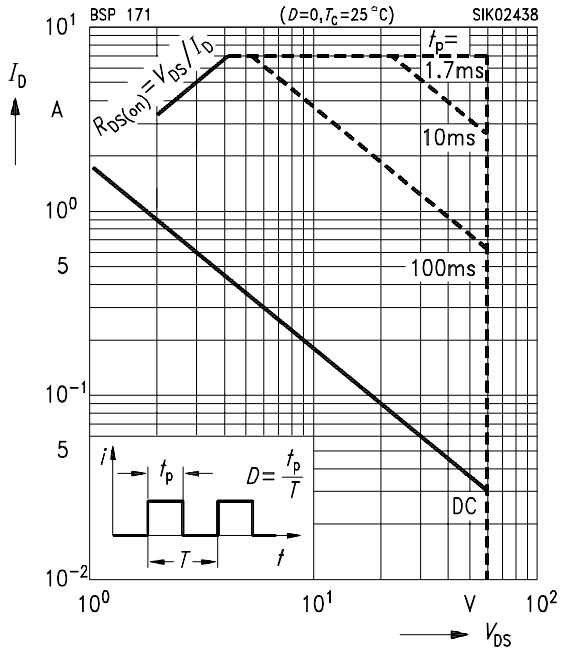
$I_D = f(T_A)$

parameter: $V_{GS} \geq$ -10 V



Safe operating area I_D=f(V_{DS})

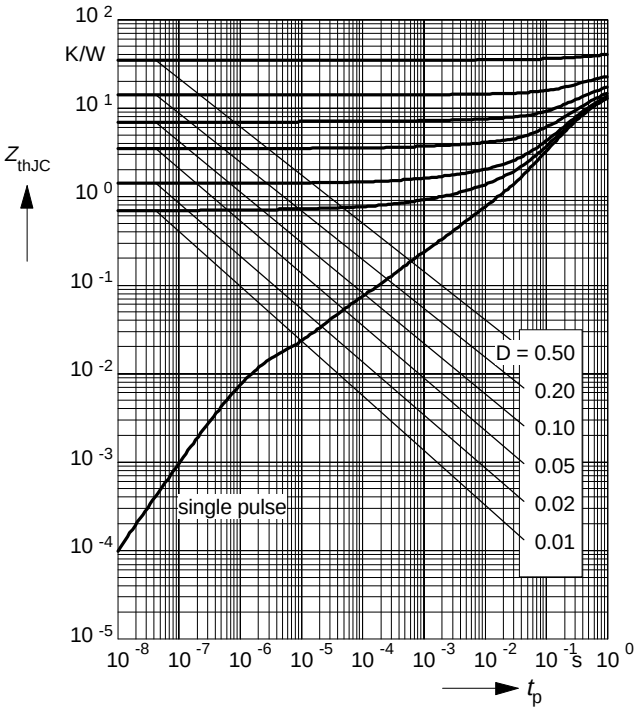
parameter : D = 0, T_C=25°C



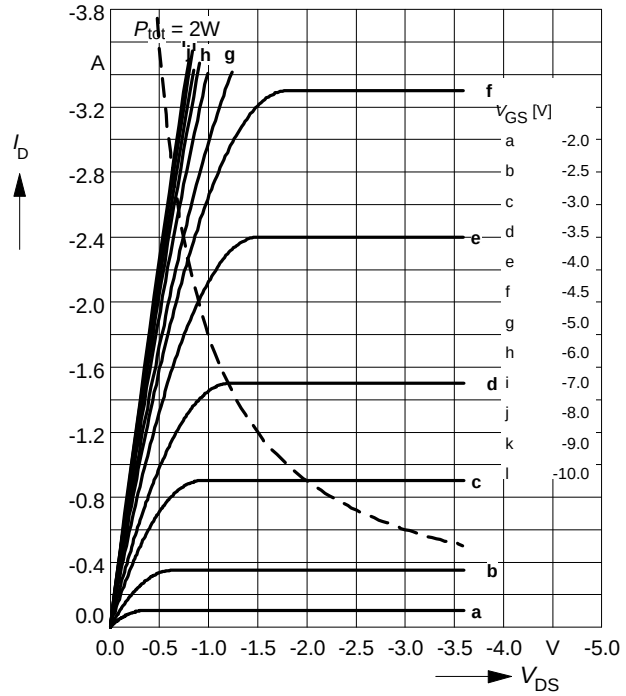
Transient thermal impedance

$Z_{th\ JA} = f(t_p)$

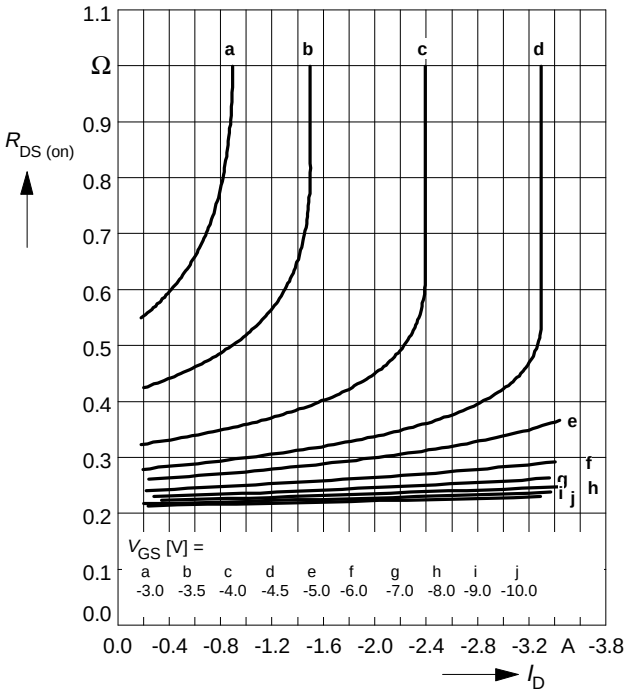
parameter: $D = t_p / T$



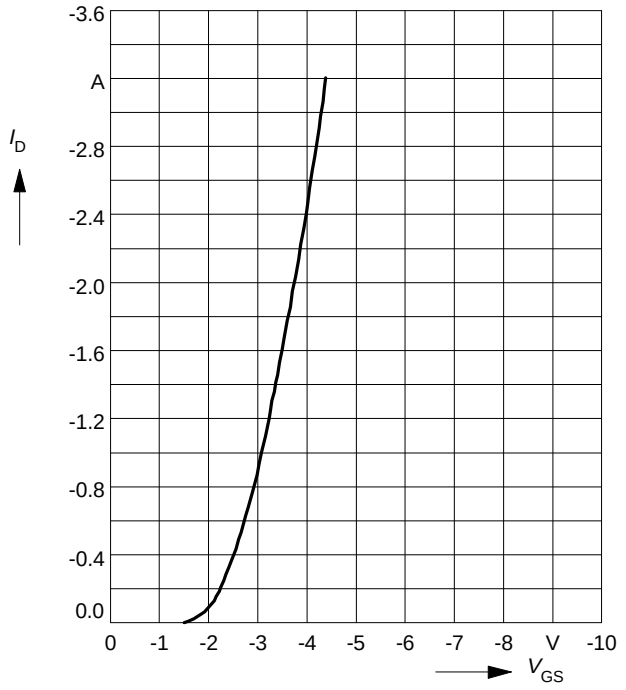
Typ. output characteristics
$I_D = f(V_{DS})$
parameter: t_p = 80 µs



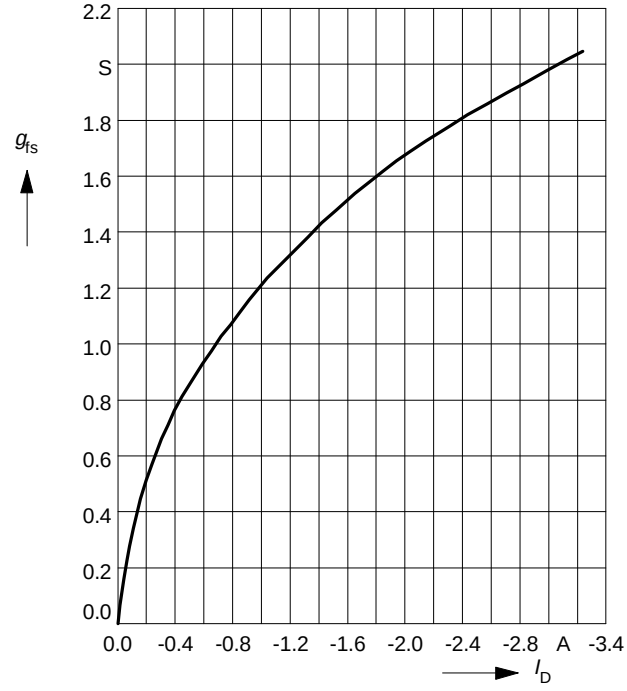
Typ. drain-source on-resistance
$R_{DS\ (on)} = f(I_D)$
parameter: t_p = 80 µs, T_j = 25 °C



Typ. transfer characteristics $I_D = f(V_{GS})$
parameter: t_p = 80 µs
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

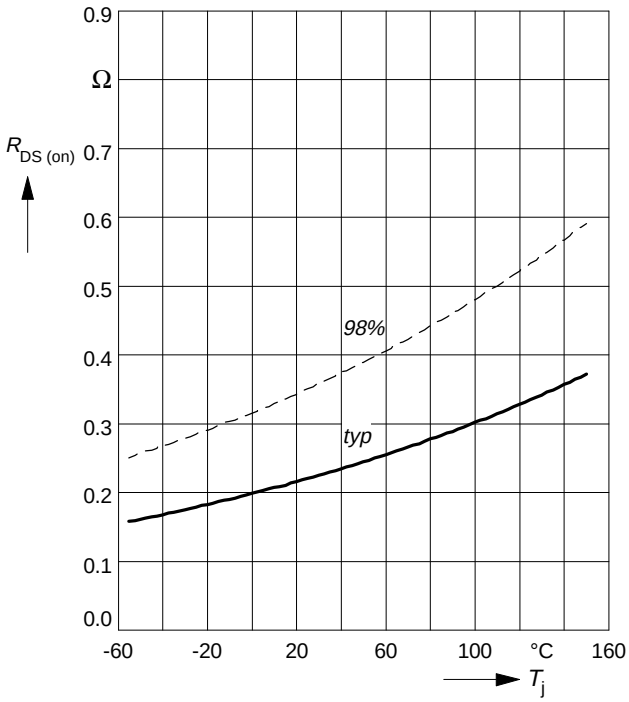


Typ. forward transconductance $g_{fs} = f(I_D)$
parameter: t_p = 80 µs,
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



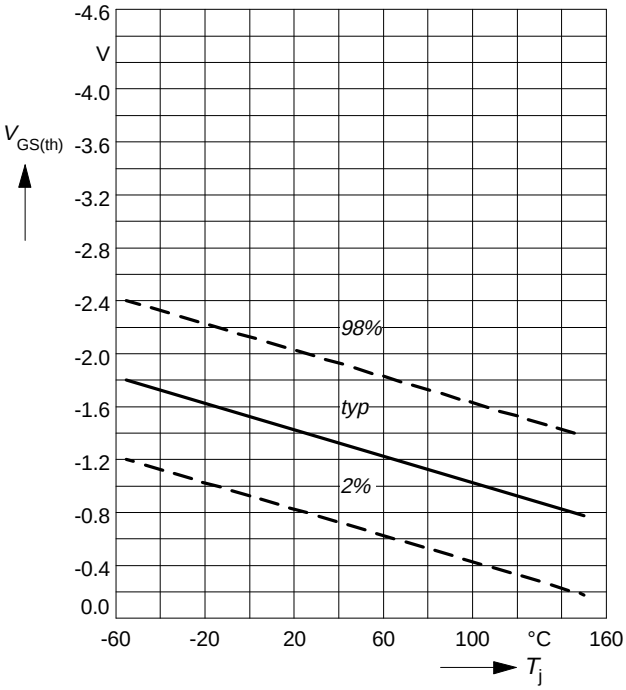
Drain-source on-resistance

$R_{DS\ (on)} = f(T_j)$
parameter: I_D = -1.7 A, V_{GS} = -10 V



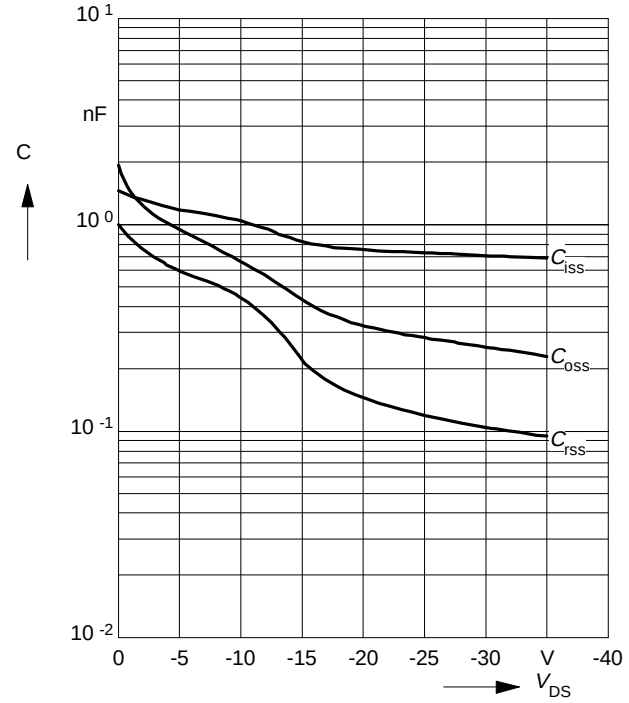
Gate threshold voltage

$V_{GS\ (th)} = f(T_j)$
parameter: $V_{GS} = V_{DS}$, I_D = -1 mA



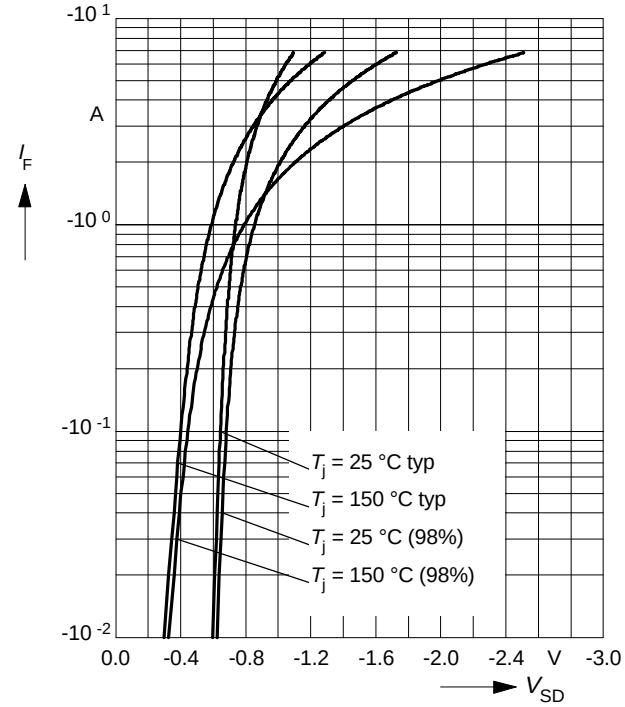
Typ. capacitances

$C = f(V_{DS})$
parameter: V_{GS}=0V, f = 1 MHz

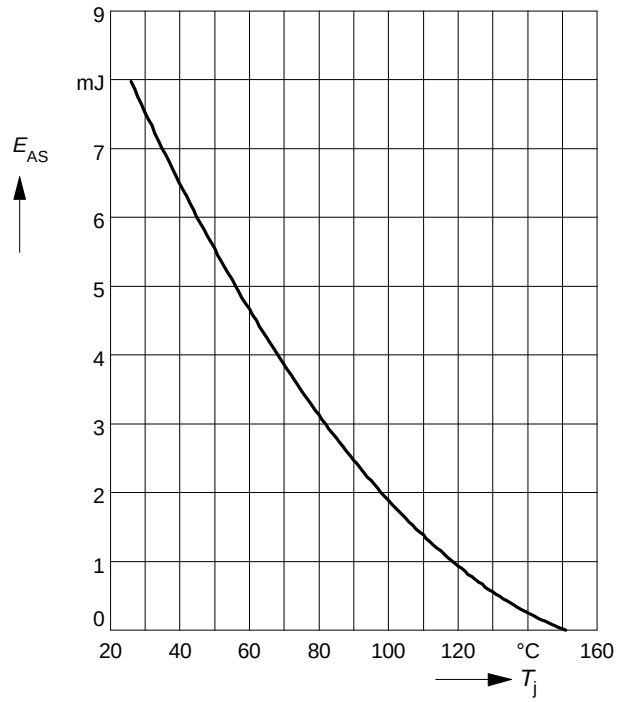


Forward characteristics of reverse diode

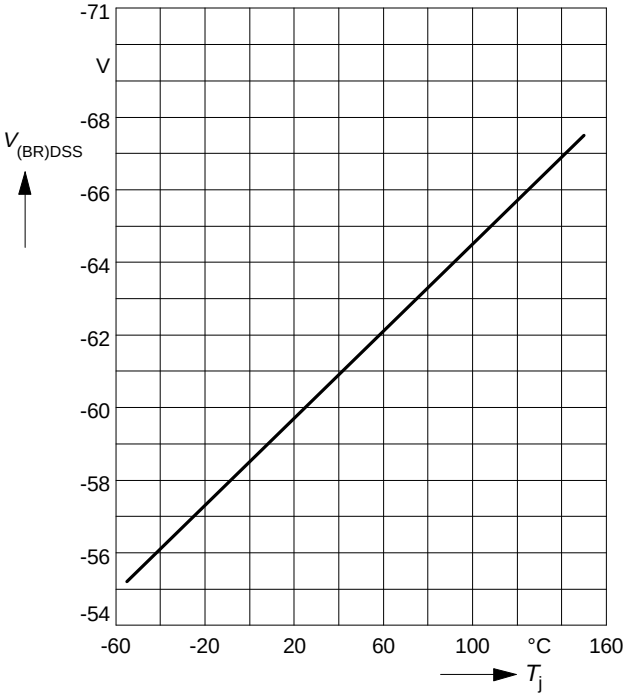
$I_F = f(V_{SD})$
parameter: T_j, t_p = 80 µs



Avalanche energy $E_{AS} = f(T_j)$
parameter: I_D = -1.7 A, V_{DD} = -25 V
R_{GS} = 25 Ω, L = 3.23 mH



Drain-source breakdown voltage
$V_{(BR)DSS} = f(T_j)$



Safe operating area I_D=f(V_{DS})
parameter : D = 0.01, T_C=25°C

